

# S3D065V004E SiC Schottky Diode

### Features:

- 1200V Schottky Diode
- Zero Reverse Recovery Current
- High Frequency Operation
- Positive Temperature Coefficient
- Temperature independent Switching

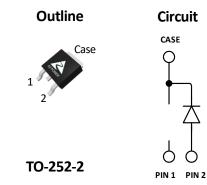
#### **Applications:**

- Switch Mode Power Supply
- Booster diodes in PFC, DC/DC
- AC/DC converters

# **Benefits:**

- Unipolar Rectifier
- Minimal switching loss
- Higher Efficiency
- Low cooling requirement

Symbol	Value	Unit	
V <sub>RRM</sub>	650	V	
IF (Tc=155ºC)	4	А	
Q <sub>C</sub>	19	nC	



## **Maximum Ratings**

Symbol	Parameter	Value	Unit	Test Conditions
V <sub>R</sub>	DC Peak Reverse Voltage	650	v	T <sub>J</sub> =25°C
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	650	V	T,=25°C
V <sub>RSM</sub>	Surge Peak Reverse Voltage	650	V	T <sub>J</sub> =25°C
IF	Continuous Forward Current	15 6.8 4	A	T <sub>c</sub> =25°C T <sub>c</sub> =135°C T <sub>c</sub> =155°C
I <sub>FRM</sub>	Repetitive Peak Forward Surge Current	40 36	А	T <sub>c</sub> =25°C, T <sub>P</sub> =10ms, Half Sine Wave Tc=125°C, T <sub>P</sub> =10ms, Half Sine Wave
I <sub>FSM</sub>	Non-Repetitive Peak Forward Surge Current	53 48	А	$T_c$ =25°C, $T_P$ =10ms, Half Sine Wave Tc=125°C, $T_P$ =10ms, Half Sine Wave
PD	Power Dissipation	54 18	w	T <sub>c</sub> =25°C Tc=125°C
T <sub>J,max</sub>	Operating Junction Temperature	175	°C	
T <sub>stg</sub>	Storage Temperature Range	-55 to 175	°C	

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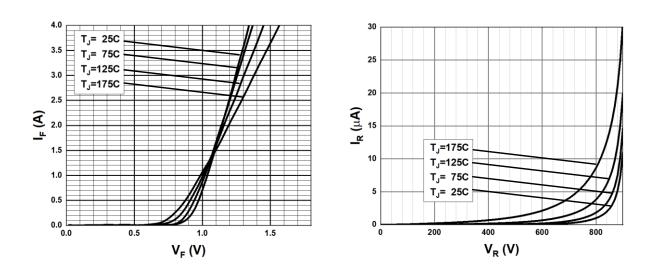
# **Thermal characteristics**

Symbol	Parameter	Min.	Тур.	Max.	Unit
R <sub>thJC</sub>	Thermal resistance		2.8		°C/W

## **Electrical Characteristics**

Gumbal	Democrator	Value		l lucit	Test Can ditions	
Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
V <sub>DC</sub>	DC Blocking Voltage	650			V	I <sub>R</sub> =100μΑ, Τ <sub>J</sub> =25°C
V	Forward Valtage		1.35	1.6	v	I <sub>F</sub> =4A, T <sub>J</sub> =25°C
VF	Forward Voltage		1.6	1.9		I <sub>F</sub> =4A, T <sub>J</sub> =175°C
	Reverse Current		1	50	μΑ	V <sub>R</sub> =650V, T <sub>J</sub> =25°C
I <sub>R</sub>	Reverse Current		5	200		V <sub>R</sub> =650V, T <sub>J</sub> =175°C
0	Tatal Canaditi va Chavea		10		nC	I <sub>F</sub> =4A, dI/dt=300A/μs
Q <sub>C</sub>	Total Capacitive Charge		19			T <sub>J</sub> =25°C, V <sub>R</sub> =400V
			174			V <sub>R</sub> =1V, T <sub>J</sub> =25°C, f=1 MHz
С	Total Capacitance		33		pF	V <sub>R</sub> =200V, T <sub>J</sub> =25°C, f=1 MHz
		30	L	V <sub>R</sub> =400V, T <sub>J</sub> =25°C, f=1 MHz		

# **Typical Performance**



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#### **Fig. 1 Forward Characteristics**

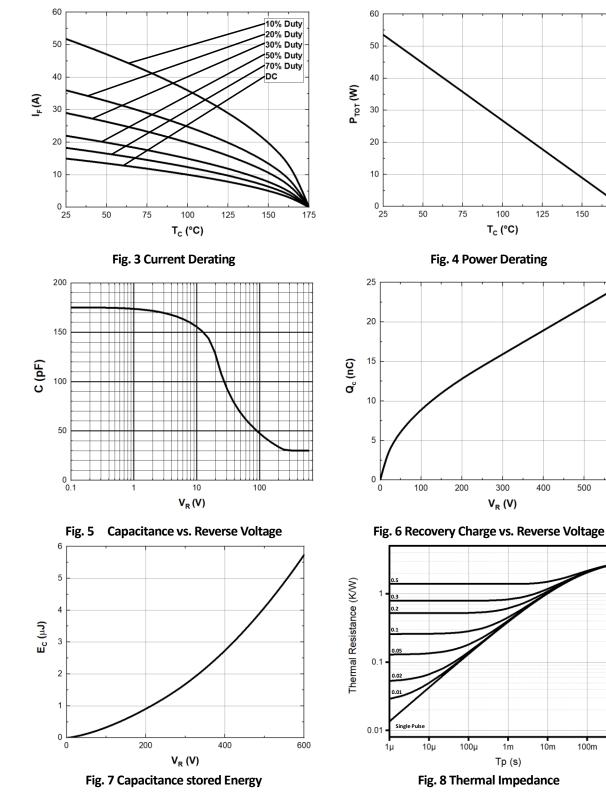
#### Fig. 2 Reverse Characteristics

S3D065V004E

175

600

SiC Schottky Diode



#### **Typical Performance**

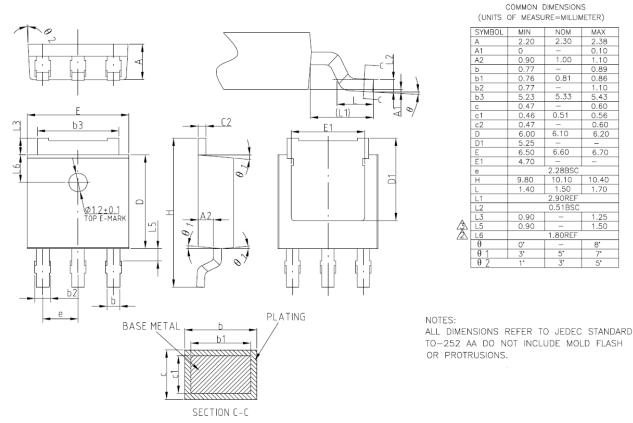
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Package TO-252-2 (Unit: mm)



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